

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	74	(spacer near (void\$1 open\$3 hole\$1)) AND (recess\$2 groove\$2 open\$3 trench\$2) AND align\$4 AND fill\$3 AND stress AND (semiconductor conduct\$3 ((epi epitaxial\$2) near (Si silicon))) AND (mandrel oxide dielectric insulat\$3).CLM.	US-PGPUB; USPAT	OR	ON	2006/11/01 13:03
S76	50	("20040204926" "5809493" "6275976" "5966524" "5715165" "4915822" "5294956" "5406289" "6404380" "6135649" "4299157" "4805408" "5826215" "4600996" "6191827" "6718291" "5548683" "6005916" "20060112049" "5715371" "5452433" "5751612" "6405132" "4797842" "5787283" "6625938" "5955737" "4924386" "5717621" "20030065689" "20040199365" "5333508" "4416121" "4484077" "4488114" "4577960" "4594077" "4614605" "4616148" "4630445" "4789294" "4831658" "4862440" "4875202" "4931743" "4963955" "5224172" "5324689" "5416048" "5434483").pn.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/31 14:07
S77	1209	(recess\$2 groove\$2 open\$3 trench\$2) WITH (stress near2 material\$1)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/31 14:34
S78	71	S77 and cmos	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/31 14:22
S79	55	(part portion) near (recess\$2 groove\$2 open\$3 trench\$2) WITH (stress near2 material\$1)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/31 14:31
S80	156	(recess\$2 groove\$2 open\$3 trench\$2) with fill\$3 with (stress near2 material\$1)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/10/31 14:43

EAST Search History

S81	1789	438/427.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/11/01 07:59
S82	1125	438/199.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/01 08:34
S83	1853	438/424.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/01 09:51
S84	623	438/435.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/01 10:07
S85	228	438/426.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/01 10:12
S86	1526	257/E21.546.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/01 10:36
S87	93	257/E21.547.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2006/11/01 10:36
S88	10533	(recess\$2 groove\$2 open\$3 trench\$2) with fill\$3 with (polysilicon "SiO.sub.2" SiGe SiN SiON)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/11/01 10:44
S89	336	(recess\$2 groove\$2 open\$3 trench\$2) with fill\$3 with ((epi epitaxial\$2) near (Si silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/11/01 12:55
S90	63	S88 with S89	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/11/01 10:47
S91	128	S88 and S89	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/11/01 10:47